

2SK1070

Silicon N-Channel Junction FET

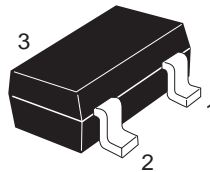
REJ03G0574-0200
(Previous ADE-208-1175 (Z))
Rev.2.00
Mar.14.2005

Application

- Low frequency / High frequency amplifier

Outline

RENESAS Package code: PLSP0003ZB-A
(Package name: MPAK)



1. Drain
2. Source
3. Gate

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Gate to drain voltage	V_{GDO}	-22	V
Gate to source voltage	V_{GSO}	-22	V
Drain current	I_D	50	mA
Gate current	I_G	10	mA
Channel power dissipation	P_{ch}	150	mW
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

Electrical Characteristics

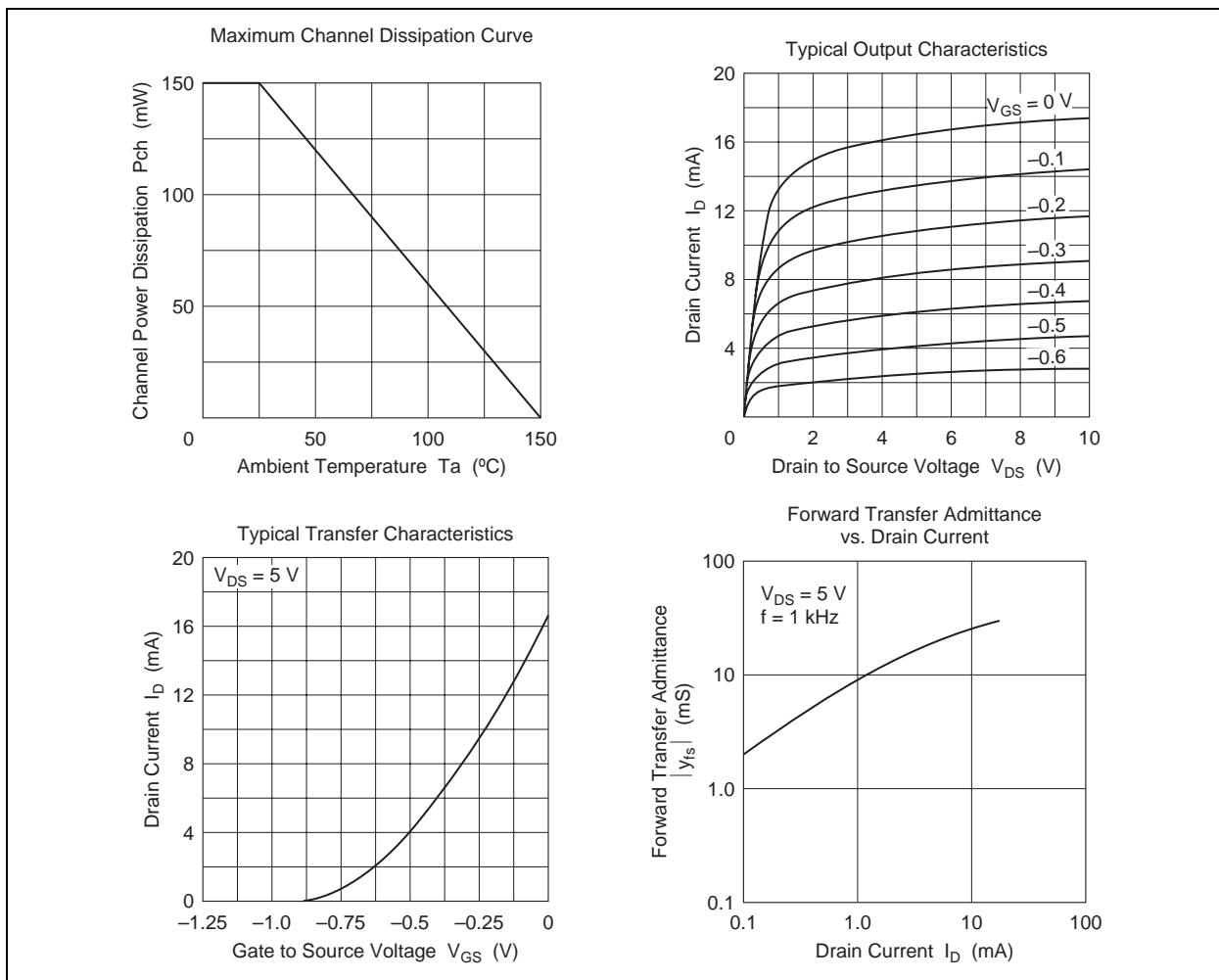
(Ta = 25°C)

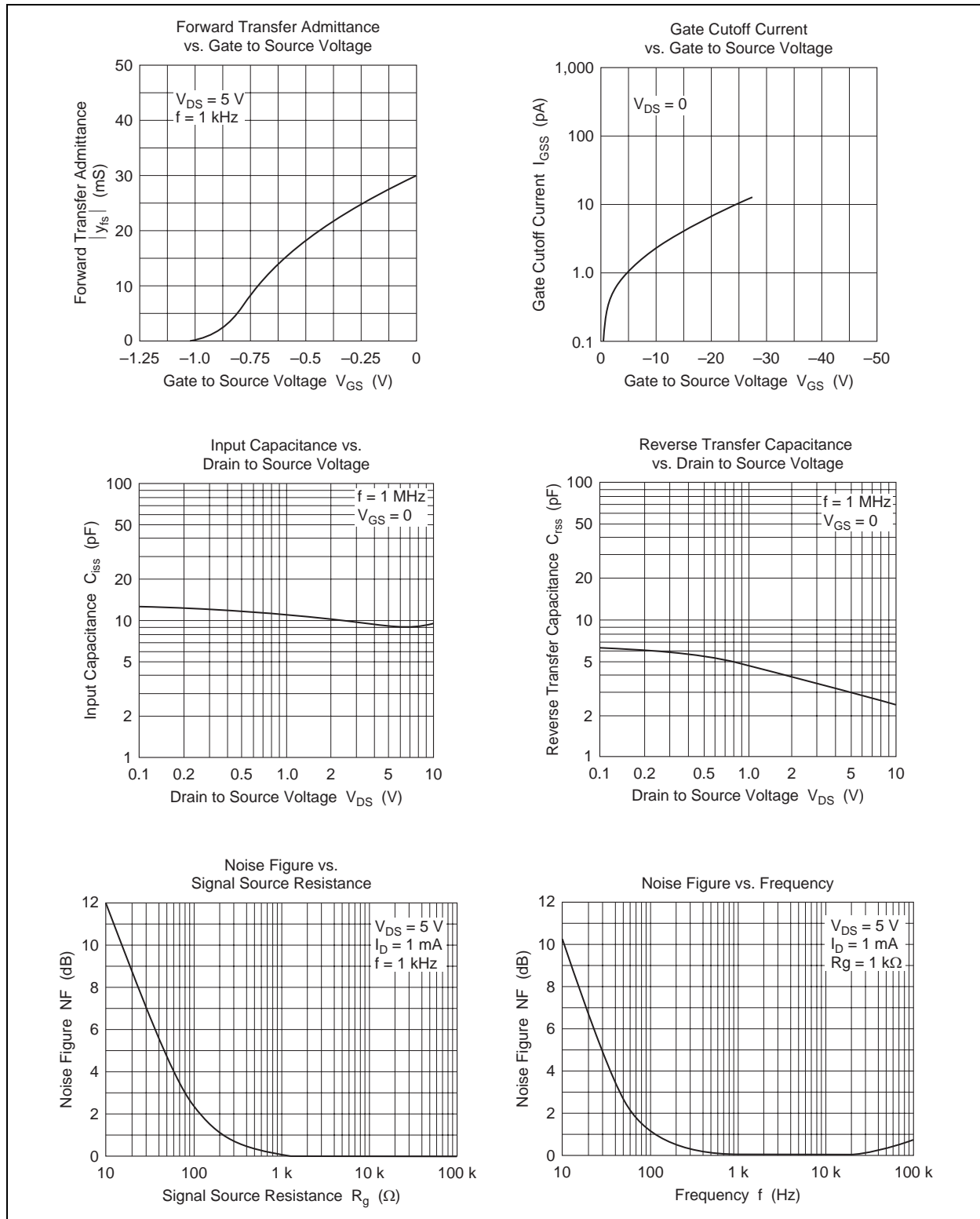
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Gate cutoff current	I_{GSS}	—	—	-10	nA	$V_{GS} = -15\text{ V}$, $V_{DS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	-22	—	—	V	$I_G = -10\ \mu\text{A}$, $V_{DS} = 0$
Drain current	I_{DSS}^{*1}	12	—	40	mA	$V_{DS} = 5\text{ V}$, $V_{GS} = 0$, Pulse test
Gate to source cutoff voltage	$V_{GS(off)}$	0	—	-2.5	V	$V_{DS} = 5\text{ V}$, $I_D = 10\ \mu\text{A}$
Forward transfer admittance	$ y_{fs} $	20	30	—	mS	$V_{DS} = 5\text{ V}$, $V_{GS} = 0$, $f = 1\text{ kHz}$
Input capacitance	C_{iss}	—	9	—	pF	$V_{DS} = 5\text{ V}$, $V_{GS} = 0$, $f = 1\text{ MHz}$

Notes: 1. The 2SK1070 is grouped by I_{DSS} as follows.

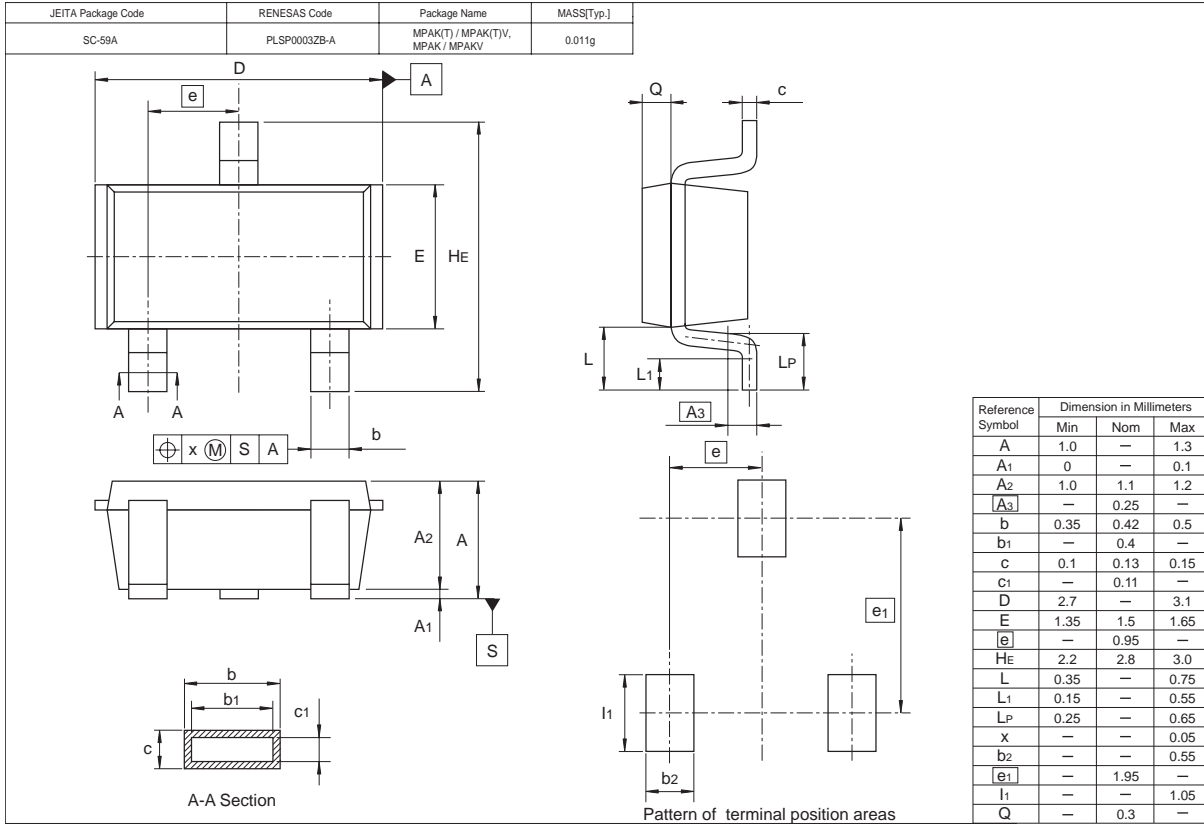
Grade	C	D	E
Mark	PIC	PID	PIE
I_{DSS}	12 to 22	18 to 30	27 to 40

Main Characteristics





Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SK1070PICTL-E	3000	φ178 mm reel, 8 mm Emboss Taping
2SK1070PIDTL-E	3000	φ178 mm reel, 8 mm Emboss Taping
2SK1070PIETL-E	3000	φ178 mm reel, 8 mm Emboss Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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